

Amendments to the Claims:

The following listing of claims replaces all other versions of claims previously presented.

Listing of Claims:

Claim 1 (withdrawn): A semiconductor device comprising:
a BGA substrate having one principal plane furnished with a large number of solder balls, said solder balls constituting a ball grid array;
a semiconductor chip mounted on another principal plane of said BGA substrate, said semiconductor chip being electrically connected to said BGA substrate by metal wires; and
chip capacitors mounted on said semiconductor chip to reduce power source noise.

Claim 2 (currently amended): A semiconductor device comprising:
a BGA substrate having one principal plane furnished with a large number of solder balls;
a first semiconductor chip having a first side and an opposite side, said first semiconductor chip including bumps and active regions, said bumps and active regions being formed on a the first side of the semiconductor chip, said bumps serving as electrodes, said first semiconductor chip being attached to another principal plane of said BGA substrate through the bumps; and
a first chip capacitor attached to ~~said the~~ active regions of said first semiconductor chip ~~or to the opposite side of said active regions of said first semiconductor chip, said first chip capacitor serving to reduce power source noise,~~

wherein a thickness of said first chip capacitor is less than a thickness of the bumps.

Claim 3 (currently amended): The A semiconductor device according to claim 2,
comprising:

a BGA substrate having one principal plane furnished with a large number of solder
balls;

a first semiconductor chip having a first side and an opposite side, said first
semiconductor chip including bumps and active regions formed on the first side, said first
semiconductor chip being attached to another principal plane of said BGA substrate through
the bumps; and

a first chip capacitor attached to the opposite side of said first semiconductor chip,
wherein said first semiconductor chip further includes through-type via contacts vias
extending from said the active regions to said the opposite side in of said first semiconductor
chip, and said first chip capacitor is electrically connected to said the active regions through
said through-type via contacts the vias.

Claim 4 (withdrawn): The semiconductor device according to claim 2, further
comprising:

a second semiconductor chip mounted on said opposite side of said active regions
of said first semiconductor chip, said second semiconductor chip being electrically
connected to said BGA substrate by metal wires; and

a second chip capacitor attached to said second semiconductor chip as well as a
first chip capacitor attached to said active region of said first semiconductor chip, said
second chip capacitor serving to reduce power source noise.

Claim 5 (withdrawn): The semiconductor device according to claim 1, further comprising:

a conductive radiator attached to said another principal plane of said BGA substrate, said conductive radiator covering said semiconductor chip; and

a shield plane incorporated in said BGA substrate, said shield plane constituting a shield of said semiconductor chip in combination with said conductive radiator; wherein said conductive radiator and said shield plane are connected to ground potential.

Claim 6 (withdrawn): The semiconductor device according to claim 2, further comprising:

a conductive radiator attached to said another principal plane of said BGA substrate, said conductive radiator covering said first semiconductor chip; and

a shield plane incorporated in said BGA substrate, said shield plane constituting a shield of said first semiconductor chip in combination with said conductive radiator; wherein said conductive radiator and said shield plane are connected to ground potential.

Claim 7 (withdrawn): The semiconductor device according to claim 6, further comprising a heat transfer member interposed between said opposite side of said active regions of said semiconductor chip and said conductive radiator.

Claim 8 (withdrawn): The semiconductor device according to claim 5, further comprising a radiating fin attached to an external surface of said conductive radiator.

Claim 9 (withdrawn): The semiconductor device according to claim 6, further comprising a radiating fin attached to an external surface of said conductive radiator.

Claim 10 (withdrawn): A semiconductor device comprising:
a semiconductor chip including bumps and active regions, said bumps serving as electrodes and being formed on one principal plane of said semiconductor chip, said active region being formed on the opposite side as said bumps;
wherein chip capacitors can be attached to said active regions of said semiconductor chip, and said chip capacitors are served to reduce power source noise.

Claim 11 (withdrawn): The semiconductor device according to claim 10, further comprising a BGA substrate having one principal plane furnished with a large number of solder balls, said solder balls constituting a ball grid array;
wherein said semiconductor chip is attached to said one principal plane of said BGA substrate by means of said bumps.

Claim 12 (withdrawn): The semiconductor device according to claim 10, wherein said semiconductor chip further has through-type via contacts extending from said active regions to a bump mounting surface thereof in said semiconductor chip, and said through-type via contact is served to ensure electrical connection between said active regions and said bumps.

Claim 13 (withdrawn): The semiconductor device according to claim 10, further comprising:

a system substrate;
a plurality of mounting pads furnished on one principal plane of said system substrate, said plurality of mounting pads being electrically connected to said bumps of said semiconductor chip;

chip capacitors mounted either on said one principal plane of said system substrate or on a back thereof, said chip capacitors serving to reduce power source noise; and

a sealing resin member for sealing said semiconductor chip.

Claim 14 (withdrawn): The semiconductor device according to claim 13, further comprising a plurality of rework mounting pads furnished on said one principal plane of said system substrate in contiguous to said mounting pads.

Claim 15 (withdrawn): The semiconductor device according to claim 13, further comprising a plurality of semiconductor chips layered on said semiconductor chip, each of said layered semiconductor chips including active regions on one surface thereof, bumps on another surface thereof, and a through-type via contacts extending from said one surface to said another surface in said semiconductor chips, said active regions and said bumps being electrically connected through said through-type via contacts.

Claim 16 (new): The semiconductor device according to claim 2, wherein said first chip capacitor is disposed among the bumps.